

N-Channel Enhancement Mode MOSFET

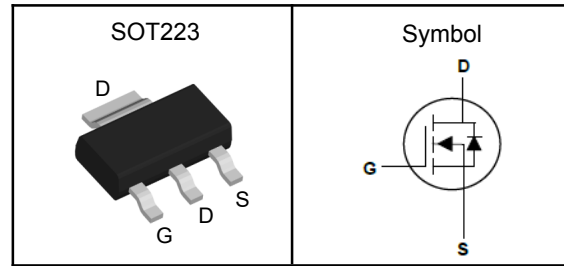
Features

- Fast switching speed
- Reliable and Rugged
- ROHS Compliant
- 100% UIS and Rg Tested

Applications

- Power Management in Desktop Computer
- DC/DC Converters

Pin Description



V_{DSS}	150	V
$R_{DS(ON)-Typ}$	260	m Ω
I_D	2	A

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$, Unless Otherwise Noted)

Symbol	Parameter	N-Channel	Unit
V_{DSS}	Drain-Source Voltage	150	V
V_{GSS}	Gate-Source Voltage	± 20	V
T_J	Maximum Junction Temperature	-55 to 150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$I_{DM}^{①}$	Pulse Drain Current Tested	6	A
I_D	Continuous Drain Current	2	A
P_D	Maximum Power Dissipation	2	W

Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ^① (Max)	62.5	$^\circ\text{C}/\text{W}$

Note ① : Max. current is limited by bonding wire.

Note ② : UIS tested and pulse width are limited by maximum junction temperature 150 $^\circ\text{C}$.

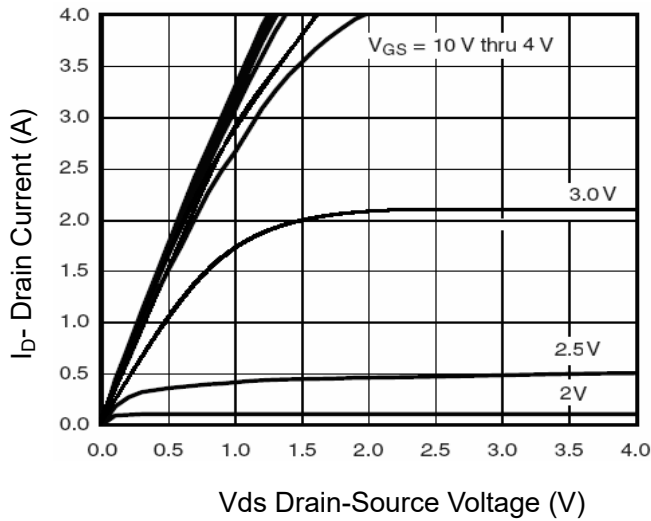
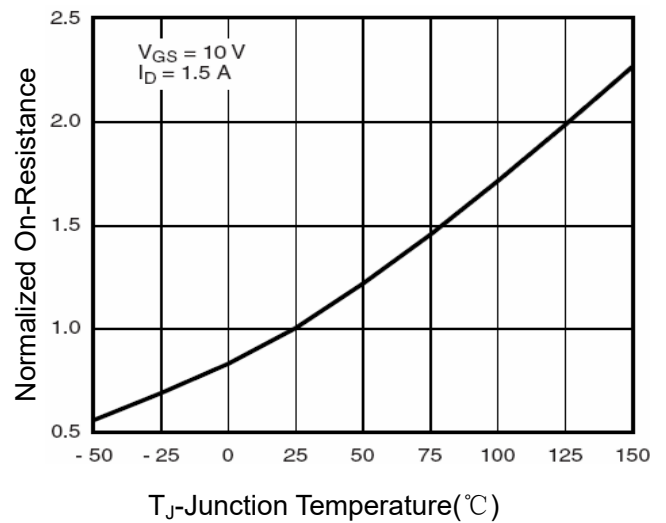
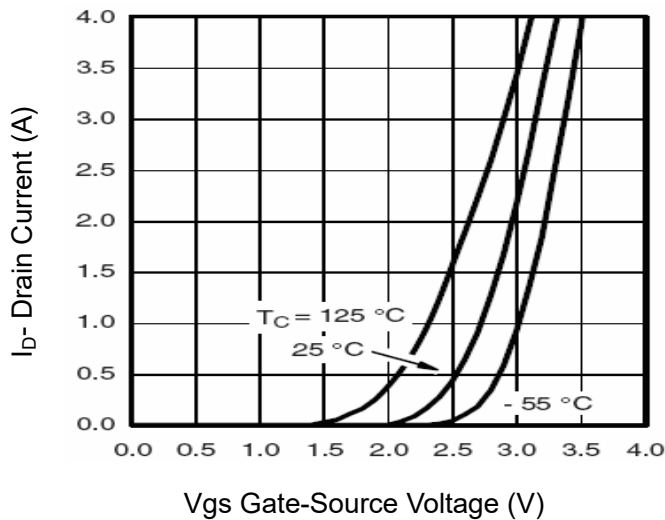
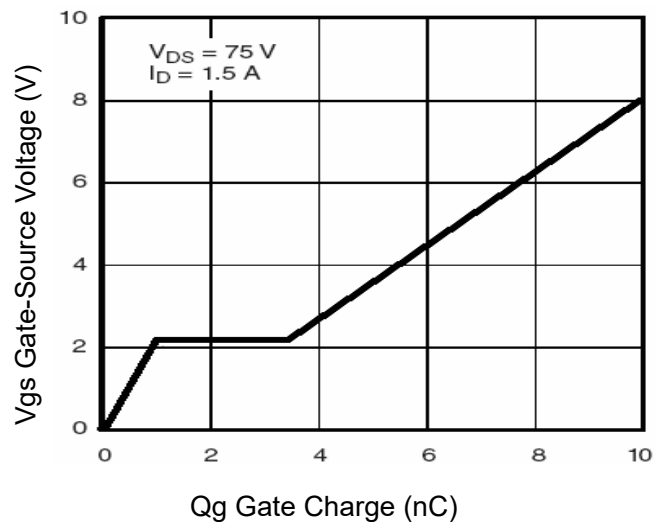
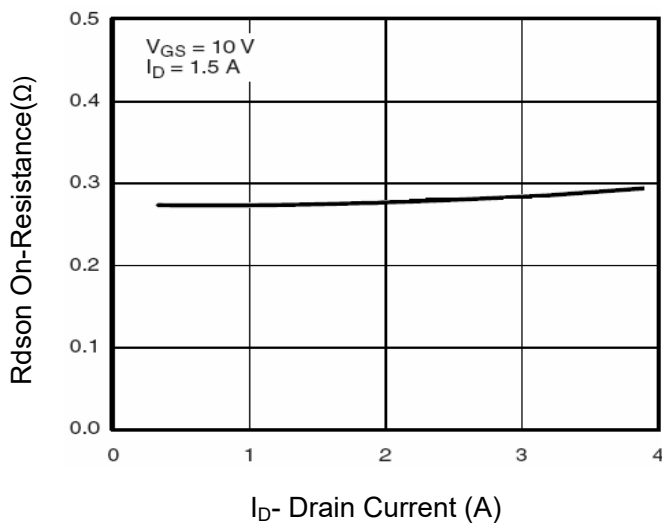
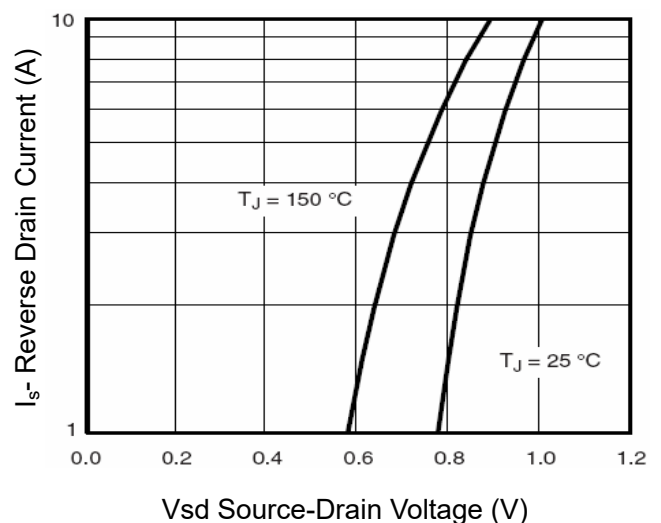
Note ③ : Surface Mounted on 1in² FR-4 board with 1oz.

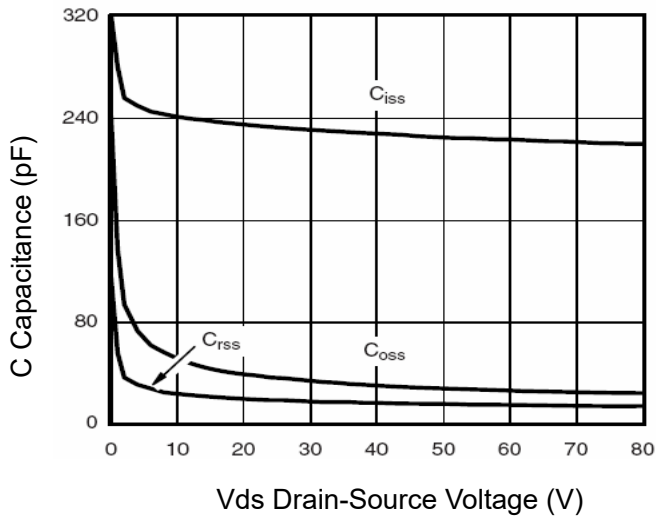
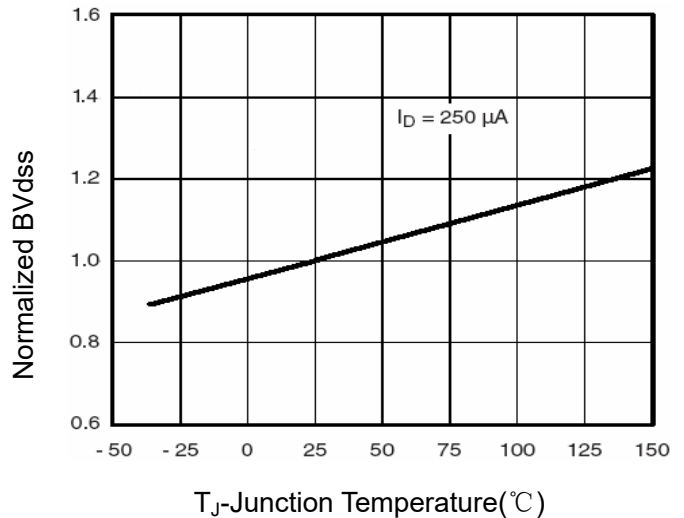
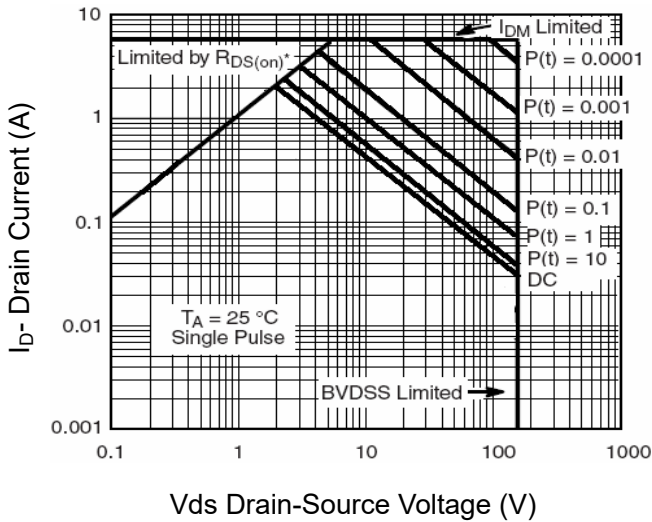
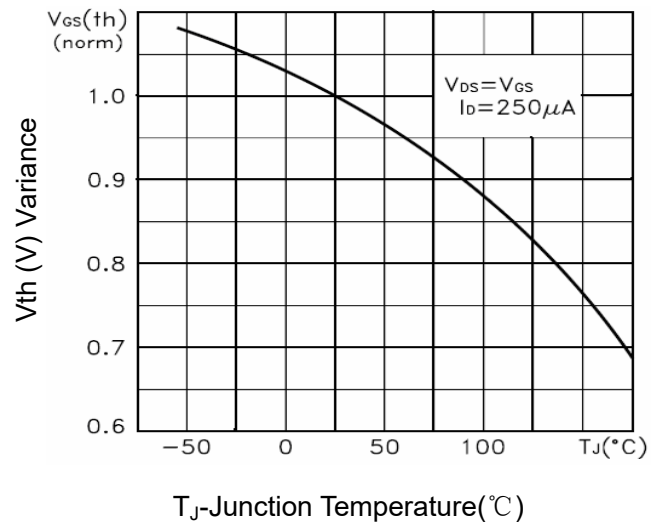
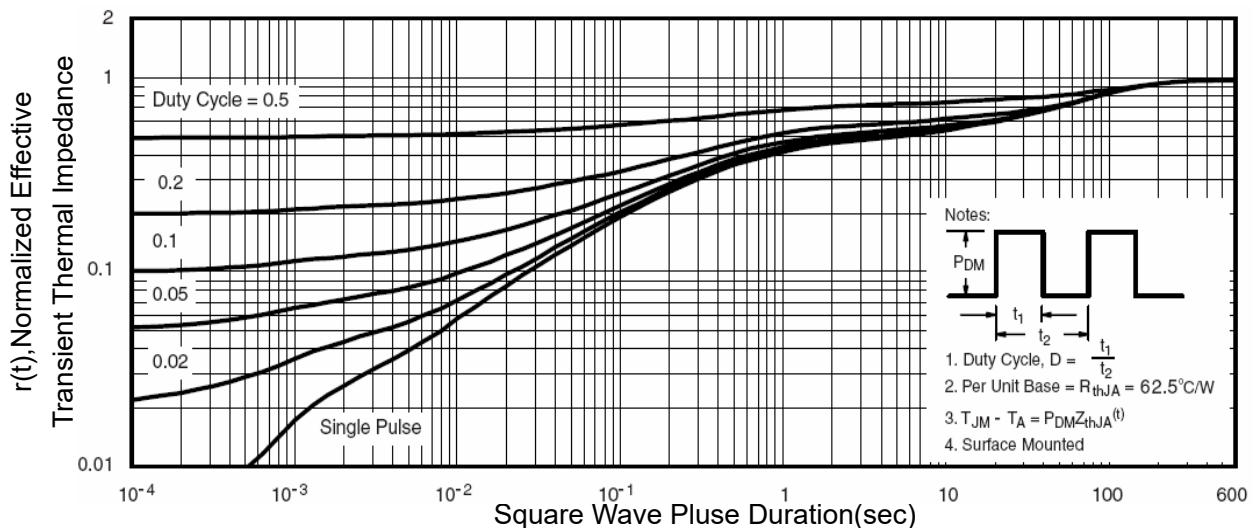
**N-Channel Enhancement Mode MOSFET****Electrical Characteristics** ($T_J=25^\circ\text{C}$, Unless Otherwise Noted)

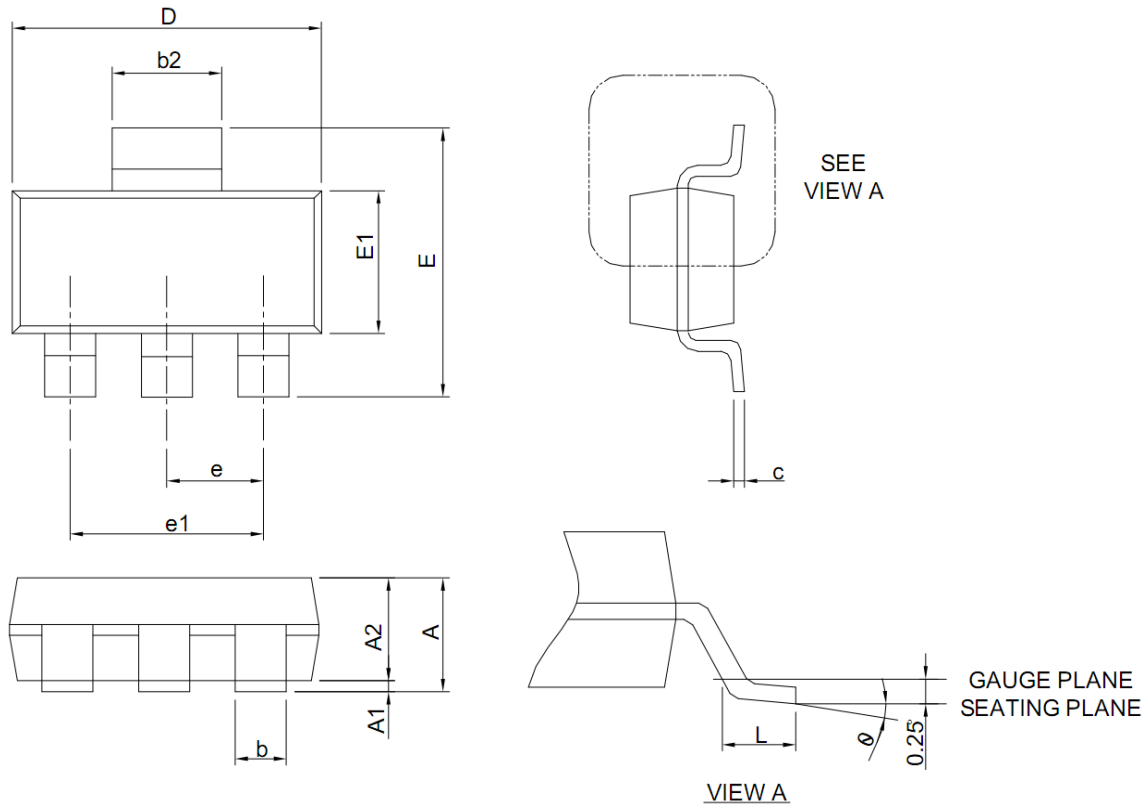
Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Static Electrical Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	150	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=150V, V_{GS}=0V$	---	---	1	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.5	---	2.5	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
$R_{DS(on)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_D=1.5A$	---	260	300	$m\Omega$
Dynamic Characteristics ^⑤						
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=25V,$ Freq.=1MHz	---	235	---	pF
C_{oss}	Output Capacitance		---	36	---	
C_{rss}	Reverse Transfer Capacitance		---	20	---	
$T_{d(on)}$	Turn-on Delay Time	$V_{DD}=75V, I_D=1A, R_L=75\Omega,$ $V_{GS}=10V, R_G=6\Omega$	---	8	---	nS
T_r	Turn-on Rise Time		---	10	---	
$T_{d(off)}$	Turn-off Delay Time		---	20	---	
T_f	Turn-off Fall Time		---	15	---	
Q_g	Total Gate Charge	$V_{DS}=75V, V_{GS}=10V,$ $I_D=1.5A$	---	8	---	nC
Q_{gs}	Gate-Source Charge		---	1.4	---	
Q_{gd}	Gate-Drain Charge		---	2.1	---	
Source-Drain Characteristics ($T_J=25^\circ\text{C}$)						
V_{SD}	Diode Forward Voltage _z	$V_{GS}=0V, I_S=2A, T_J=25^\circ\text{C}$	---	---	1.2	V

Note ④ : Pulse test (pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$).

Note ⑤ : Guaranteed by design, not subject to production testing.

N-Channel Enhancement Mode MOSFET
Typical Characteristics

Figure 1 Output Characteristics

Figure 4 Rdson- Junction Temperature

Figure 2 Transfer Characteristics

Figure 5 Gate Charge

Figure 3 Rdson- Drain Current

Figure 6 Source- Drain Diode Forward

N-Channel Enhancement Mode MOSFET

Figure 7 Capacitance vs Vds

Figure 9 BV_{DSS} vs Junction Temperature

Figure 8 Safe Operation Area

Figure 10 $V_{GS(th)}$ vs Junction Temperature

Figure 11 Normalized Maximum Transient Thermal Impedance

N-Channel Enhancement Mode MOSFET
SOT223 Package Outline Data


Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	1.50	1.65	1.80	A1	0.02	0.06	0.10
A2	1.50	1.60	1.70	b	0.66	0.72	0.80
b2	2.90	3.00	3.10	c	0.23	0.30	0.35
D	6.30	6.50	6.70	E	6.70	7.00	7.30
E1	3.30	3.50	3.70	e	2.30 REF		
e1	4.60 REF			L	0.75	--	1.15
θ	0°	--	10°				